

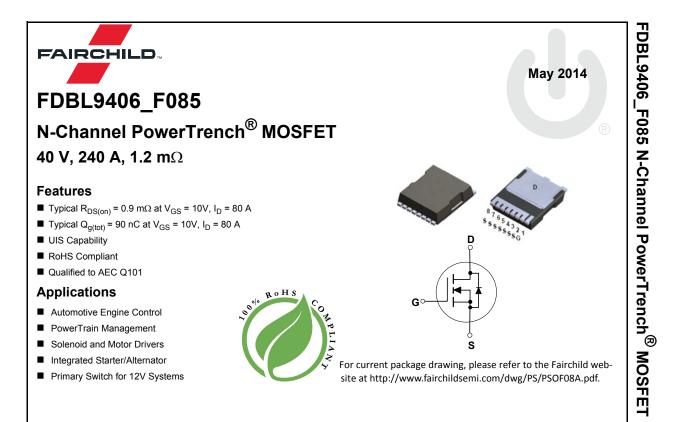
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## **MOSFET Maximum Ratings** T<sub>1</sub> = 25°C unless otherwise noted.

Symbol	Parameter		Ratings	Units	
V <sub>DSS</sub>	Drain-to-Source Voltage		40	V	
V <sub>GS</sub>	Gate-to-Source Voltage		±20	V	
ID	Drain Current - Continuous (V <sub>GS</sub> =10) (Note 1)	T <sub>C</sub> =25°C	240	Α	
	Pulsed Drain Current	T <sub>C</sub> = 25°C	See Figure 4		
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 2)	316	mJ	
P <sub>D</sub>	Power Dissipation		300	W	
	Derate Above 25°C		2.0	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature		-55 to + 175	°C	
R <sub>0JC</sub>	Thermal Resistance, Junction to Case		0.5	°C/W	
R <sub>0JA</sub>	Maximum Thermal Resistance, Junction to Ambient (Note 3)		43	°C/W	

### Notes:

1: Current is limited by bondwire configuration.

2: Starting T<sub>J</sub> = 25°C, L = 0.1mH,  $I_{AS}$  = 79.5A,  $V_{DD}$  = 40V during inductor charging and  $V_{DD}$  = 0V during time in avalanche. 3:  $R_{0,JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

# Package Marking and Ordering Information

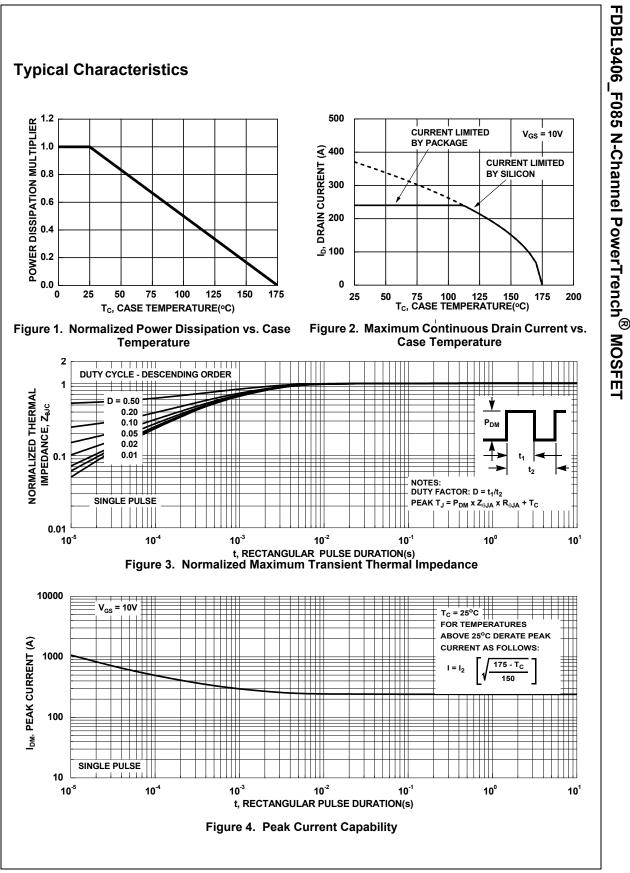
Device Marking	Device	Package			
FDBL9406	FDBL9406_F085	MO-299A	-	-	-

Symbol	Parameter	Test Conditions		Тур.	Max.	Units
off Cha	racteristics					
B <sub>VDSS</sub>	Drain-to-Source Breakdown Voltage	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	40	-	-	V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	$\begin{array}{c c} V_{DS} = 40V, & T_{J} = 25^{\circ}C \\ V_{GS} = 0V & T_{J} = 175^{\circ}C \text{ (Note 4)} \end{array}$	-	-	1	μA mA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$	-	-	±100	nA
	racteristics					1
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.0	3.2	4.0	V
_	Drain to Source On Resistance	$I_{\rm D} = 80$ A, $T_{\rm J} = 25^{\rm o}$ C	-	0.90	1.20	mΩ
R <sub>DS(on)</sub>		$V_{GS}$ = 10V T <sub>J</sub> = 175°C (Note 4)	-	1.64	1.86	mΩ
<b>Dynami</b> C <sub>iss</sub>	c Characteristics			7735	-	pF
C <sub>oss</sub>	Output Capacitance	$-V_{DS} = 25V, V_{GS} = 0V,$	-	2160	_	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1MHz	-	129	-	pF
R <sub>q</sub>	Gate Resistance	f = 1MHz	-	2.5	-	Ω
Q <sub>g(ToT)</sub>	Total Gate Charge at 10V		-	90	107	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 10V$ $V_{DD} = 32V$ $V_{GS} = 0 \text{ to } 2V$ $I_D = 80A$	-	13.5	15.5	nC
Q <sub>gs</sub>	Gate-to-Source Gate Charge		-	43	-	nC
Q <sub>gd</sub>	Gate-to-Drain "Miller" Charge		-	10	-	nC
Switchi	ng Characteristics			-	102	ns
t <sub>d(on)</sub>	Turn-On Delay			33	-	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 20V, I <sub>D</sub> = 80A,	-	40	-	ns
t <sub>d(off)</sub>	Turn-Off Delay	$V_{GS} = 10V, R_{GEN} = 6\Omega$	-	47	-	ns
t <sub>f</sub>	Fall Time		-	23	-	ns
t <sub>off</sub>	Turn-Off Time		-	-	91	ns
	ource Diode Characteristics			1	1	
V.	Source to Drain Diade Valtage	I <sub>SD</sub> =80A, V <sub>GS</sub> = 0V	-	-	1.25	V
V <sub>SD</sub>	Source-to-Drain Diode Voltage	I <sub>SD</sub> = 40A, V <sub>GS</sub> = 0V	-	-	1.2	V
t <sub>rr</sub>	Reverse-Recovery Time	$I_{F} = 80A, dI_{SD}/dt = 100A/\mu s,$	-	91	107	ns
	Reverse-Recovery Charge	V <sub>DD</sub> =32V		128	167	nC

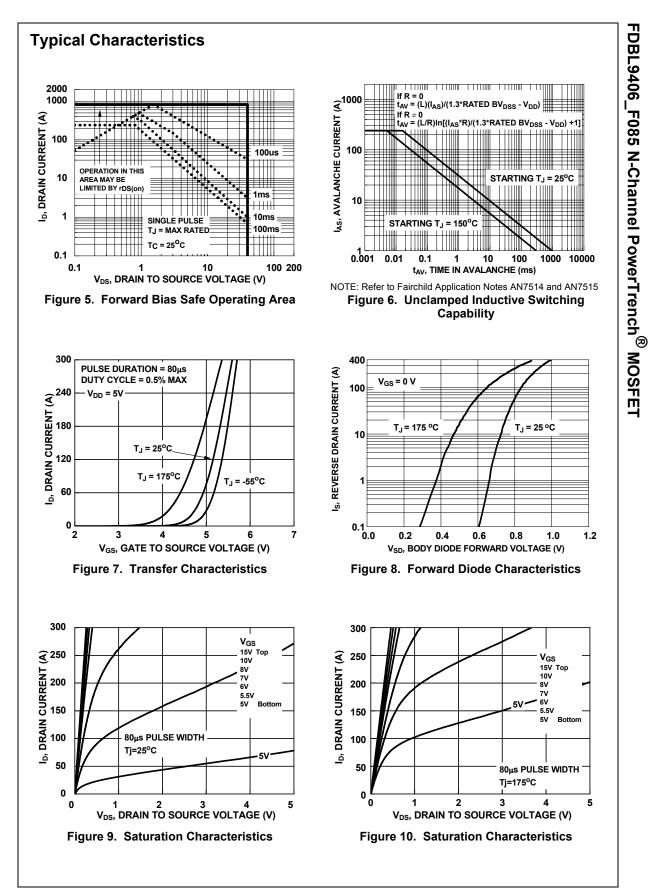
FDBL9406\_F085 N-Channel PowerTrench<sup>®</sup> MOSFET

## Note:

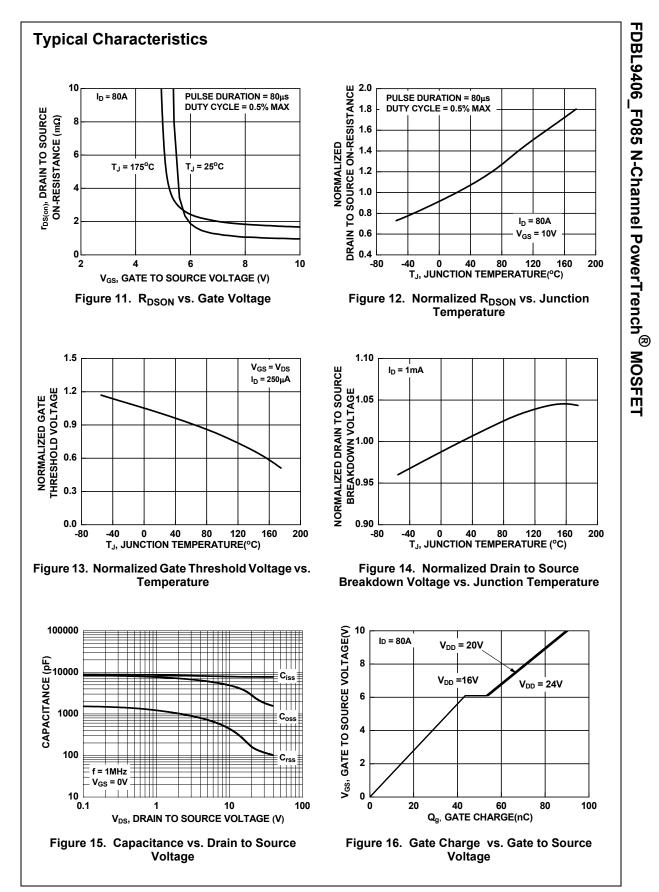
4: The maximum value is specified by design at  $T_J$  = 175°C. Product is not tested to this condition in production.



FDBL9406\_F085 Rev. C2



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FDBL9406\_F085 Rev. C2



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